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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

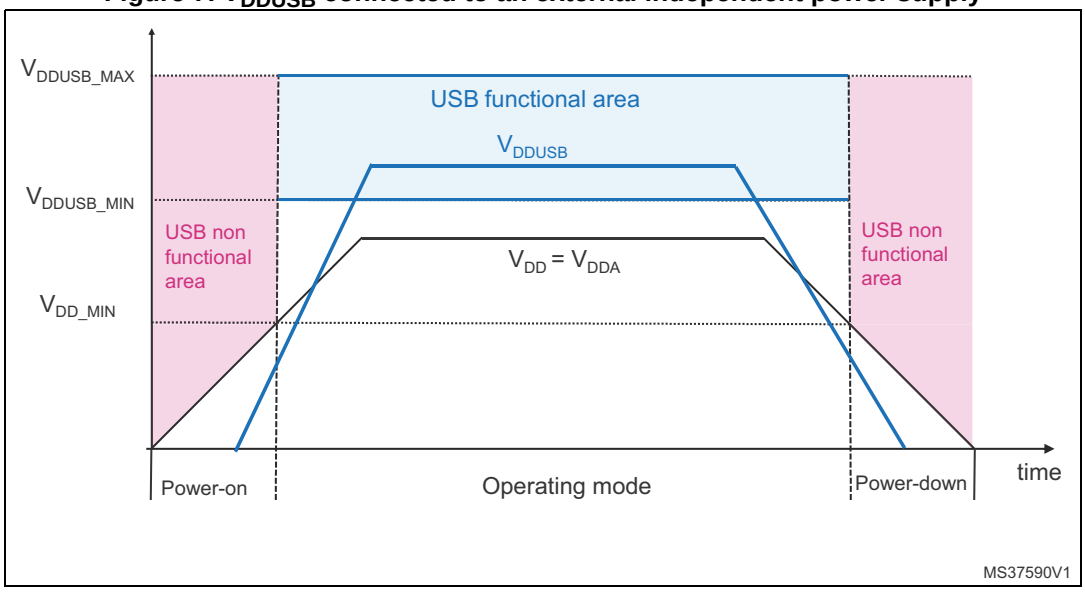
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SAI, SDIO, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	161
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f469bet6

The following conditions must be respected:

- During power-on phase ($V_{DD} < V_{DD\_MIN}$), V_{DDUSB} should be always lower than V_{DD}
- During power-down phase ($V_{DD} < V_{DD\_MIN}$), V_{DDUSB} should be always lower than V_{DD}
- V_{DDUSB} rising and falling time rate specifications must be respected.
- In operating mode phase, V_{DDUSB} could be lower or higher than VDD:
  - If USB (USB OTG_HS/OTG_FS) is used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DDUSB_MIN} and V_{DDUSB_MAX}.The V_{DDUSB} supplies both USB transceivers (USB OTG_HS and USB OTG_FS).
  - If only one USB transceiver is used in the application, the GPIOs associated to the other USB transceiver are still supplied by V_{DDUSB}.
  - If USB (USB OTG_HS/OTG_FS) is not used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DD_MIN} and V_{DD_MAX}.

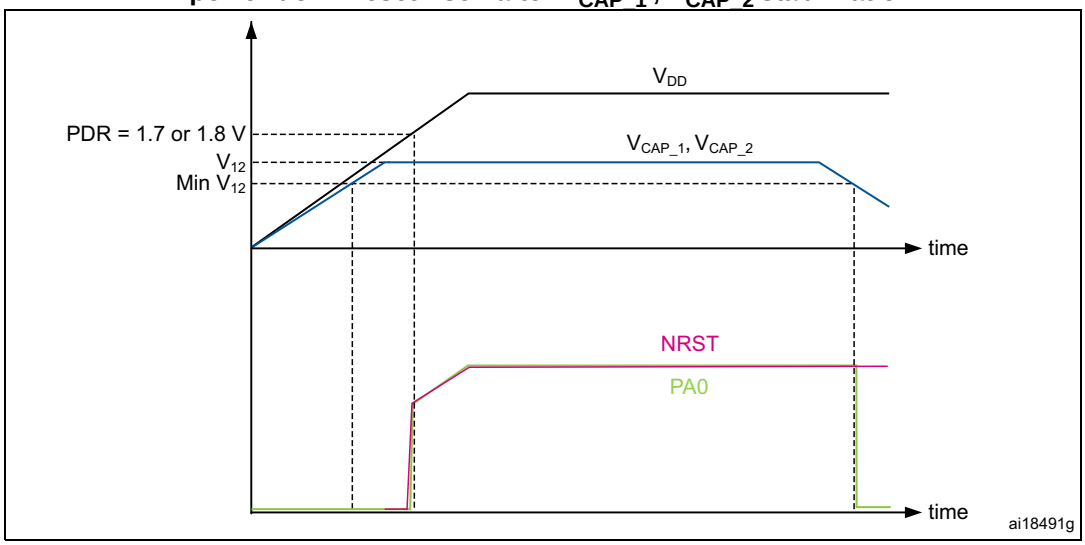
Figure 7. V_{DDUSB} connected to an external independent power supply



The DSI (Display Serial Interface) sub-system uses several power supply pins which are independent from the other supply pins:

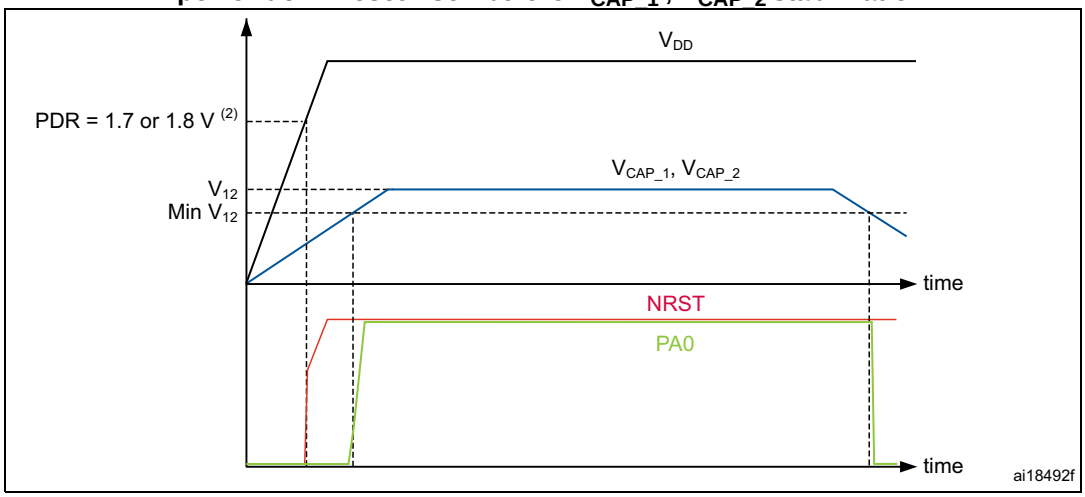
- VDDDSI is an independent DSI power supply dedicated for DSI Regulator and MIPI D-PHY. This supply must be connected to global VDD.
- VCAPDSI pin is the output of DSI Regulator (1.2V) which must be connected externally to VDD12DSI.
- VDD12DSI pin is used to supply the MIPI D-PHY, and to supply clock and data lanes pins. An external capacitor of 2.2 uF must be connected on VDD12DSI pin.
- VSSDSI pin is an isolated supply ground used for DSI sub-system.
- If DSI functionality is not used at all, then:
  - VDDDSI pin must be connected to global VDD.
  - VCAPDSI pin must be connected externally to VDD12DSI but the external capacitor is no more needed.
  - VSSDSI pin must be grounded.

Figure 11. Startup in regulator OFF: slow V_{DD} slope - power-down reset risen after V_{CAP_1}, V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 12. Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1}, V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

2.43 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

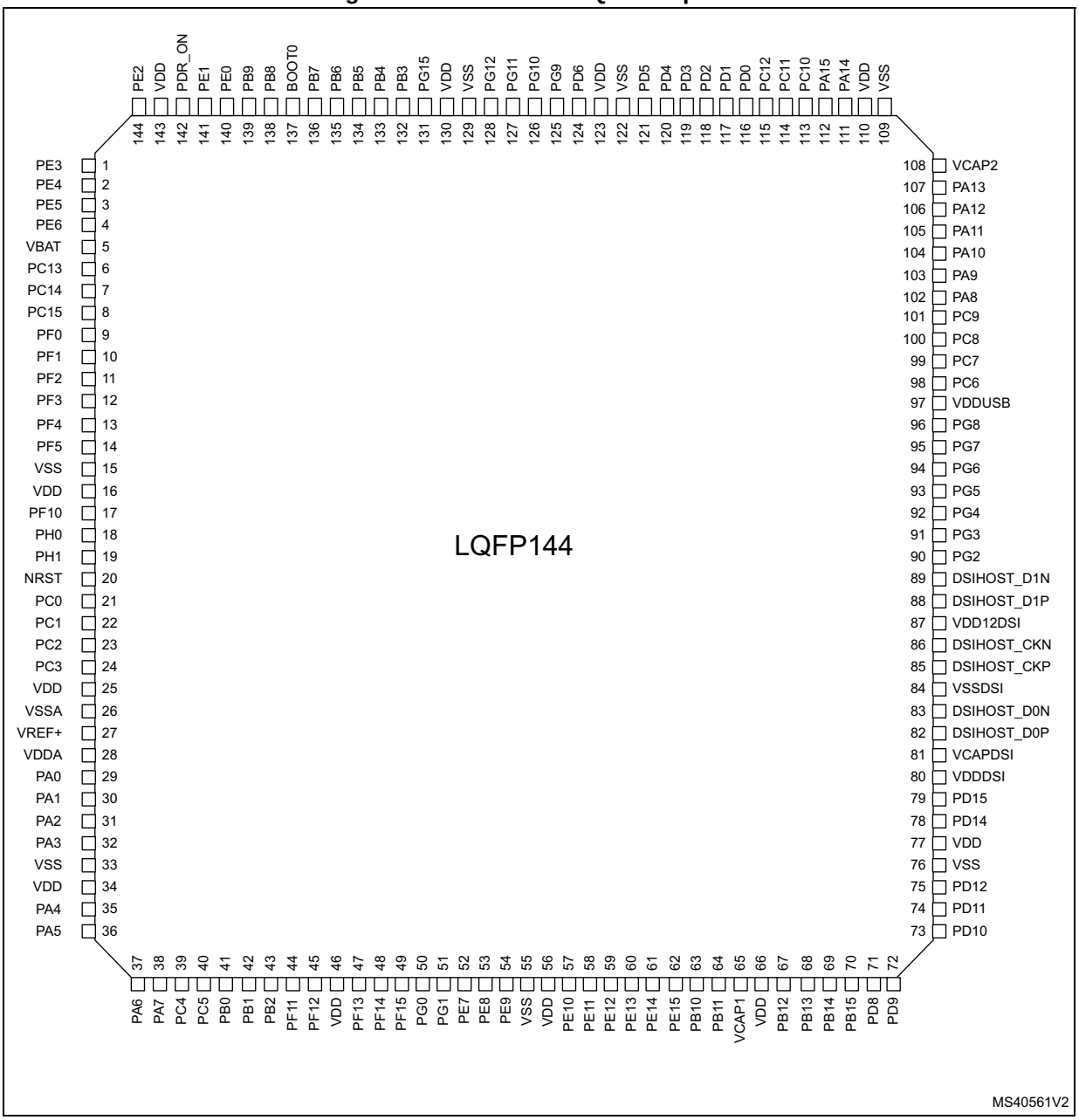
Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

2.44 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F46x through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

Figure 14. STM32F46x LQFP144 pinout



1. The above figure shows the package top view.

Table 10. STM32F469xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)(1)	Pin types	I/O structures	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	WLCSP168	UFBGA176	LQFP176	LQFP208	TFBGA216						
-	9	F3	G10	E2	16	16	D2	PF0	I/O	FT		I2C2_SDA, FMC_A0, EVENTOUT	-
-	10	G3	H10	H3	17	17	E2	PF1	I/O	FT		I2C2_SCL, FMC_A1, EVENTOUT	-
-	11	G5	G12	H2	18	18	G2	PF2	I/O	FT		I2C2_SMBA, FMC_A2, EVENTOUT	-
-	-	-	-	-	-	19	E3	PI12	I/O	FT		LCD_HSYNC, EVENTOUT	-
-	-	-	-	-	-	20	G3	PI13	I/O	FT		LCD_VSYNC, EVENTOUT	-
-	-	-	-	-	-	21	H3	PI14	I/O	FT		LCD_CLK, EVENTOUT	-
-	12	H4	H11	J2	19	22	H2	PF3	I/O	FT	(5)	FMC_A3, EVENTOUT	ADC3_IN9
-	13	L4	J10	J3	20	23	J2	PF4	I/O	FT	(5)	FMC_A4, EVENTOUT	ADC3_IN14
-	14	H3	H12	K3	21	24	K3	PF5	I/O	FT	(5)	FMC_A5, EVENTOUT	ADC3_IN15
7	15	G7	J11	G2	22	25	H6	VSS	S	-	-	-	-
8	16	G8	J12	G3	23	26	H5	VDD	S	-	-	-	-
-	-	-	-	K2	24	27	K2	PF6	I/O	FT	(5)	TIM10_CH1, SPI5_NSS, SAI1_SD_B, UART7_Rx, QUADSPI_BK1_IO3, EVENTOUT	ADC3_IN4
-	-	-	-	K1	25	28	K1	PF7	I/O	FT	(5)	TIM11_CH1, SPI5_SCK, SAI1_MCLK_B, UART7_Tx, QUADSPI_BK1_IO2, EVENTOUT	ADC3_IN5
-	-	-	-	L3	26	29	L3	PF8	I/O	FT	(5)	SPI5_MISO, SAI1_SCK_B, TIM13_CH1, QUADSPI_BK1_IO0, EVENTOUT	ADC3_IN6
-	-	-	-	L2	27	30	L2	PF9	I/O	FT	(5)	SPI5_MOSI, SAI1_FS_B, TIM14_CH1, QUADSPI_BK1_IO1, EVENTOUT	ADC3_IN7
-	17	H1	K10	L1	28	31	L1	PF10	I/O	FT	(5)	QUADSPI_CLK, DCMI_D11, LCD_DE, EVENTOUT	ADC3_IN8
9	18	G2	K11	G1	29	32	G1	PH0-OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN
10	19	G1	K12	H1	30	33	H1	PH1-OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT
11	20	H2	H9	J1	31	34	J1	NRST	I/O	RST	-		
12	21	M1	J9	M2	32	35	M2	PC0	I/O	FT	(5)	OTG_HS_ULPI_STP, FMC_SDNWE, LCD_R5, EVENTOUT	ADC123_ IN10

Table 11. FMC pin definition (continued)

Pin name	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PF8	-	-	-	-
PF9	-	-	-	-
PF10	-	-	-	-
PG6	-	-	-	-
PG7	-	-	INT	-
PE0	NBL0	NBL0	-	NBL0
PE1	NBL1	NBL1	-	NBL1
PI4	NBL2	-	-	NBL2
PI5	NBL3	-	-	NBL3
PG8	-	-	-	SDCLK
PC0	-	-	-	SDNWE
PF11	-	-	-	SDNRAS
PG15	-	-	-	SDNCAS
PH2	-	-	-	SDCKE0
PH3	-	-	-	SDNE0
PH6	-	-	-	SDNE1
PH7	-	-	-	SDCKE1
PH5	-	-	-	SDNWE
PC2	-	-	-	SDNE0
PC3	-	-	-	SDCKE0
PB5	-	-	-	SDCKE1
PB6	-	-	-	SDNE1

7. To sustain a voltage higher than VDD+0.3, the internal Pull-up and Pull-Down resistors must be disabled
8. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax}.
9. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax}.

Table 18. Limitations depending on the operating power supply range

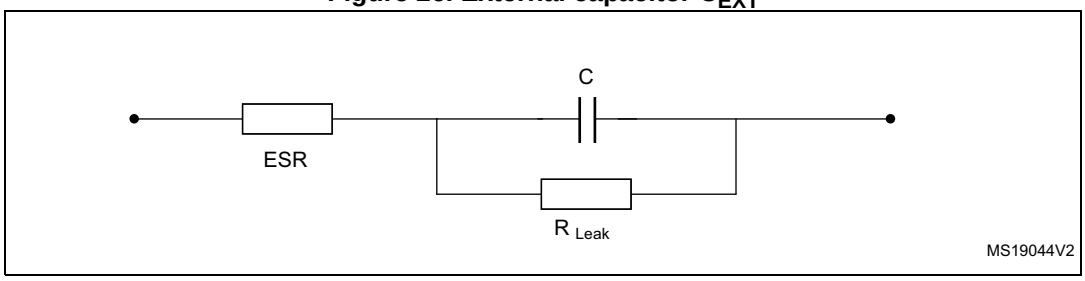
Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum HCLK frequency vs. Flash memory wait states (1)(2)	I/O operation	Possible Flash memory operations
V_{DD} = 1.7 to 2.1 V(3)	Conversion time up to 1.2 Msps	20 MHz(4)	168 MHz with 8 wait states and over-drive OFF	No I/O compensation	8-bit erase and program operations only
V_{DD} = 2.1 to 2.4 V		22 MHz	180 MHz with 8 wait states and over-drive ON		16-bit erase and program operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	180 MHz with 7 wait states and over-drive ON	I/O compensation works	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V(5)		30 MHz	180 MHz with 5 wait states and over-drive ON		32-bit erase and program operations

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 2.19.2*).
4. Prefetch is not available.
5. When V_{DDUSB} is connected to V_{DD}, the voltage range for USB full speed PHYs can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

5.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor C_{EXT} to the VCAP1/VCAP2 pins. C_{EXT} is specified in *Table 19*.

Figure 26. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 22. Reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.65	2.84	2.92	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}$(1)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	
$V_{PDRhyst}$(1)	PDR hysteresis	-	-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	
		Rising edge	2.53	2.59	2.63	
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	
		Rising edge	2.85	2.92	2.97	
$V_{BORhyst}$(1)	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}$(1)(2)	POR reset temporization	-	0.5	1.5	3.0	ms
I_{RUSH}(1)	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
E_{RUSH}(1)	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	V_{DD} = 1.7 V, T_A = 105 °C, I_{RUSH} = 171 mA for 31 µs	-	-	5.4	µC

1. Guaranteed by design.
2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

Table 25. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled), regulator ON

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in RUN mode	All Peripherals enabled(2)(3)	168	97	102	128	154	mA
			150	87	92	118	143	
			144	80	84	108	131	
			120	65	68	88	108	
			90	51	54	73	93	
			60	37	41	59	79	
			30	21	23	42	62	
			25	18	20	39	59	
		All Peripherals disabled	168	49	55	79	105	
			150	44	49	44	100	
			144	40	45	68	92	
			120	36	39	58	78	
			90	29	32	51	71	
			60	22	25	44	64	
			30	13	15	34	54	
			25	11	13	32	52	

1. Guaranteed based on test during characterization.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

Table 30. Typical and maximum current consumption in Standby mode

Symbol	Parameter	Conditions	Typ(1)			Max(2)			Unit
			T_A = 25 °C			T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
			V_{DD} = 1.7 V	V_{DD}= 2.4 V	V_{DD} = 3.3 V	V_{DD} = 3.3 V			
I_{DD_STBY}	Supply current in Standby mode	Backup SRAM ON, RTC and LSE oscillator OFF	1.7	2.5	2.9	6(3)	18	35(3)	µA
		Backup SRAM OFF, RTC and LSE oscillator OFF	1.0	1.8	2.20	5(3)	15	30(3)	
		Backup SRAM OFF, RTC ON and LSE oscillator in Power Drive mode	1.7	2.7	3.2	7	20	39	
		Backup SRAM ON, RTC ON and LSE oscillator in Power Drive mode	2.4	3.4	4.0	8	25	48	
		Backup SRAM ON, RTC ON and LSE oscillator in High Drive mode	3.2	4.2	4.8	10	29	57	
		Backup SRAM OFF, RTC ON and LSE oscillator in High Drive mode	2.5	3.5	4.1	8	25	48	

1. PDR is off for V_{DD}=1.7 V. When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional 1.2 µA
2. Based on characterization, not tested in production unless otherwise specified.
3. Based on characterization, tested in production.

Figure 35 and *Figure 36* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 35. PLL output clock waveforms in center spread mode

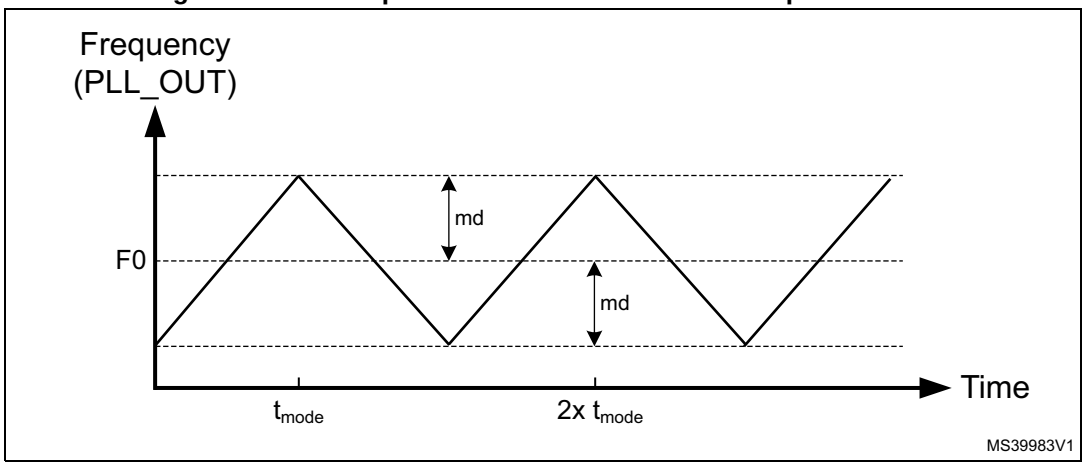
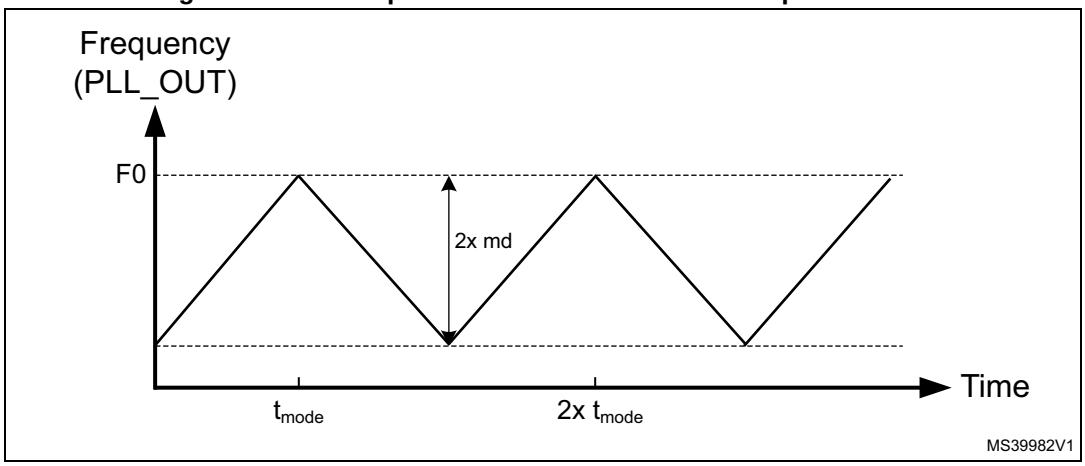


Figure 36. PLL output clock waveforms in down spread mode



5.3.13 MIPI D-PHY characteristics

The parameters given in *Table 45* and *Table 46* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 45. MIPI D-PHY characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Hi-Speed Input/Output Characteristics						
U_{INST}	UI instantaneous	-	2	-	12.5	ns

Table 45. MIPI D-PHY characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CMTX}	HS transmit common mode voltage	-	150	200	250	mV
$\|\Delta V_{CMTX}\|$	V_{CMTX} mismatch when output is Differential-1 or Differential-0	-	-	-	5	
$\|V_{OD}\|$	HS transmit differential voltage	-	140	200	270	
$\|\Delta V_{OD}\|$	V_{OD} mismatch when output is Differential-1 or Differential-0	-	-	-	14	
V_{OHHS}	HS output high voltage	-	-	-	360	
Z_{OS}	Single ended output impedance	-	40	50	62.5	Ω
ΔZ_{OS}	Single ended output impedance mismatch	-	-	-	10	%
t_{HSr} & t_{HSf}	20%-80% rise and fall time	-	100	-	0.35*UI	ps
LP Receiver Input Characteristics						
V_{IL}	Logic 0 input voltage (not in ULP State)	-	-	-	550	mV
$V_{IL-ULPS}$	Logic 0 input voltage in ULP State	-	-	-	300	
V_{IH}	Input high level voltage	-	880	-	-	
V_{hys}	Voltage hysteresis	-	25	-	-	
LP Emitter Output Characteristics						
V_{IL}	Output low level voltage	-	1.1	1.2	1.2	V
$V_{IL-ULPS}$	Output high level voltage	-	-50	-	50	mV
V_{IH}	Output impedance of LP transmitter	-	110	-	-	Ω
V_{hys}	15%-85% rise and fall time	-	-	-	25	ns
LP Contention Detector Characteristics						
V_{ILCD}	Logic 0 contention threshold	-	-	-	200	mV
V_{IHCD}	Logic 0 contention threshold	-	450	-	-	

1. Guaranteed based on test during characterization.

Table 60. I/O AC characteristics(1)(2)

OSPEEDRy [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} ≥ 2.7 V	-	-	4	MHz
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	2	
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	8	
			C_L = 10 pF, V_{DD} ≥ 1.8 V	-	-	4	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	3	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} = 1.7 V to 3.6 V	-	-	100	ns
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD}≥ 2.7 V	-	-	25	MHz
			C_L = 50 pF, V_{DD}≥ 1.8 V	-	-	12.5	
			C_L = 50 pF, V_{DD}≥ 1.7 V	-	-	10	
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	50	
			C_L = 10 pF, V_{DD}≥ 1.8 V	-	-	20	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	12.5	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} ≥ 2.7 V	-	-	10	ns
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	6	
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	20	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	10	
10	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 40 pF, V_{DD} ≥ 2.7 V	-	-	50(4)	MHz
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	100(4)	
			C_L = 40 pF, V_{DD} ≥ 1.7 V	-	-	25	
			C_L = 10 pF, V_{DD} ≥ 1.8 V	-	-	50	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	42.5	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 40 pF, V_{DD} ≥2.7 V	-	-	6	ns
			C_L = 10 pF, V_{DD} ≥ 2.7 V	-	-	4	
			C_L = 40 pF, V_{DD} ≥ 1.7 V	-	-	10	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	6	

Table 73. Dynamics characteristics: Ethernet MAC signals for SMI(1)

Symbol	Parameter	Min	Typ	Max	Unit
t_{MDC}	MDC cycle time(2.38 MHz)	400	400	403	ns
$T_{d(MDIO)}$	Write data valid time	T_{HCLK} - 1	T_{HCLK}	T_{HCLK} + 1.5	
$t_{su(MDIO)}$	Read data setup time	12.5	-	-	
$t_{h(MDIO)}$	Read data hold time	0	-	-	

1. Guaranteed based on test during characterization.

Table 74 gives the list of Ethernet MAC signals for the RMII and *Figure 52* shows the corresponding timing diagram.

Figure 52. Ethernet RMII timing diagram

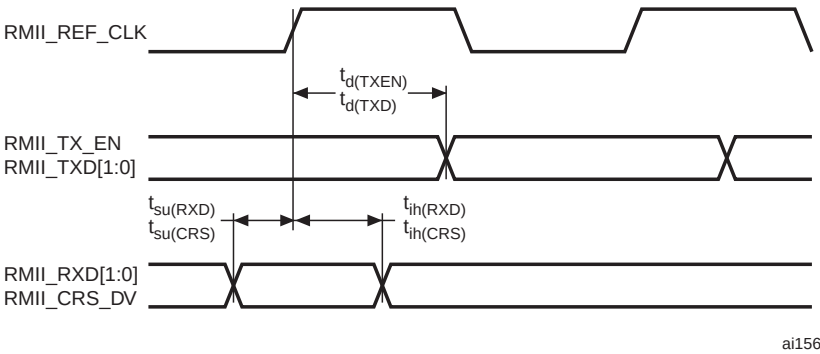


Table 111. Dynamic characteristics: SD / MMC characteristics, V_{DD} = 1.71 to 1.9 V(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	f_{pp} =50 MHz	9.5	10.5	-	ns
$t_{W(CKH)}$	Clock high time		8.5	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	f_{pp} =50 MHz	0.5	-	-	ns
t_{IH}	Input hold time HS		3.5	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	f_{pp} =50 MHz	-	13.5	14.5	ns
t_{OH}	Output hold time HS		13.0	-	-	

1. Guaranteed based on test during characterization.
2. C_{load} = 20 pF.

5.3.34 RTC characteristics

Table 112. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

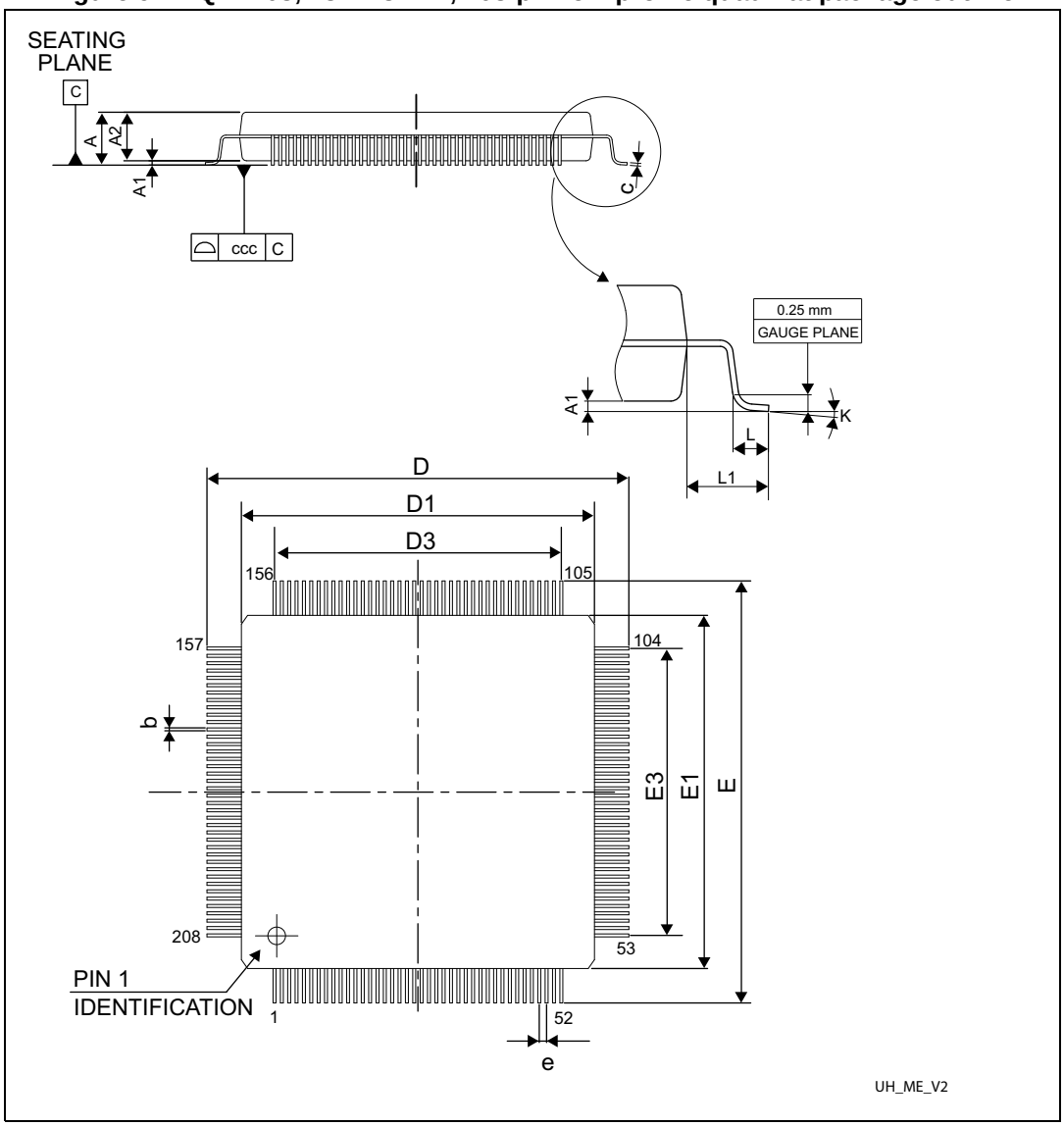
Table 113. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

6.7 LQFP208 package information

Figure 94. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package outline

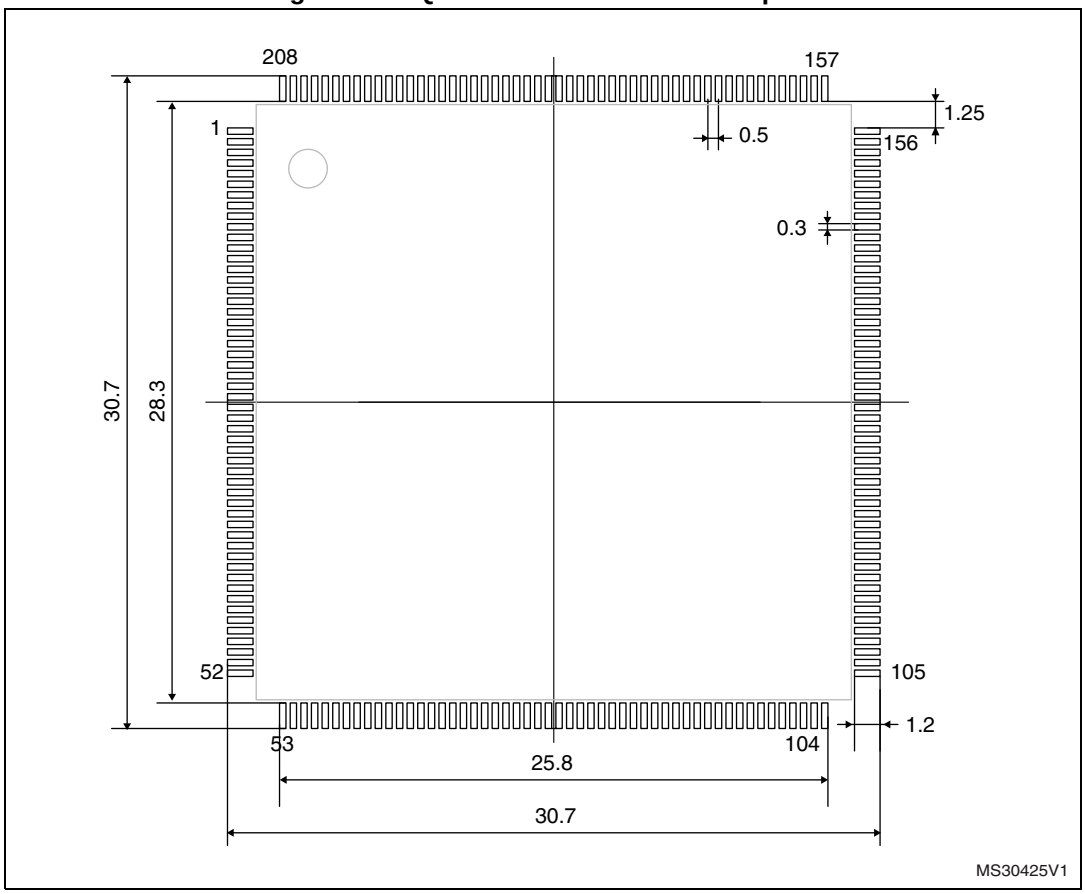


1. Drawing is not to scale.

Table 120. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	--	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106

Figure 95. LQFP208 recommended footprint



1. Dimensions are expressed in millimeters.